

2SK2539

N-Channel Junction Silicon FET High-Frequency Amp,

Analog Switch Applications

Features

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- · Large | Y_{fs} | .
- · Small Ciss.
- · Small-sized package permitting 2SK2539-applied sets to be made small and slim.
- · Adoption of FBET process.

Absolute Maximum Ratings at '	I'a = 25°C		unit
Drain-to-Source Voltage	V_{DSX}	15	V
Gate-to-Drain Voltage	V_{GDS}	-15	V
Gate Current	$I_{\mathbf{G}}$	5	mA
Drain Current	I_D	50	mA
Allowable Power Dissipation	P_{D}	200	\mathbf{mW}
Junction Temperature	Tj	150	$^{\circ}\mathrm{C}$
Storage Temperature	Tstg	-55 to +150	$^{\circ}\mathrm{C}$

Electrical Characteristics at Ta=	= 25°C		min	tvp	max	unit
G-D Breakdown Voltage		$I_G = -10 \mu A, V_{DS} = 0$	–15	ijΡ	mun	V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = -10V, V_{DS} = 0$			-1.0	nΑ
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 10 \mu A$	-0.6	-1.4	-3.0	V
Drain Current	I_{DSS}	$V_{\rm DS} = 5V, V_{\rm GS} = 0$	10.0%		50.0%	€ mA
Forward Transfer Admittance		$V_{DS} = 5V, I_D = 10 \text{mA}, f = 1 \text{kHz}$	14	21		mS

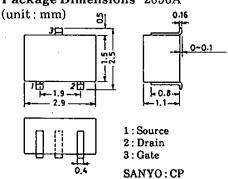
Forward Transfer Admittance	$ \mathbf{y}_{\mathrm{fs}} $ 1	$V_{DS} = 5V, I_{D} = 10 \text{ mA}, f = 1 \text{ kHz}$	14	21	mS
	\mathbf{y}_{fs} 2	$V_{DS} = 5V, V_{GS} = 0, f = 1kHz$	14	29	mS
Input Capacitance	Ciss	$V_{DS} = 5V$, $V_{GS} = 0$, $f = 1MHz$		4.9	рF
Reverse Transfer Capacitance	\mathbf{Crss}	$V_{DS} = 5V$, $V_{GS} = 0$, $f = 1MHz$		1.4	pF

* The 2SK2539 is classified by I_{DSS} as follows: (unit: mA)

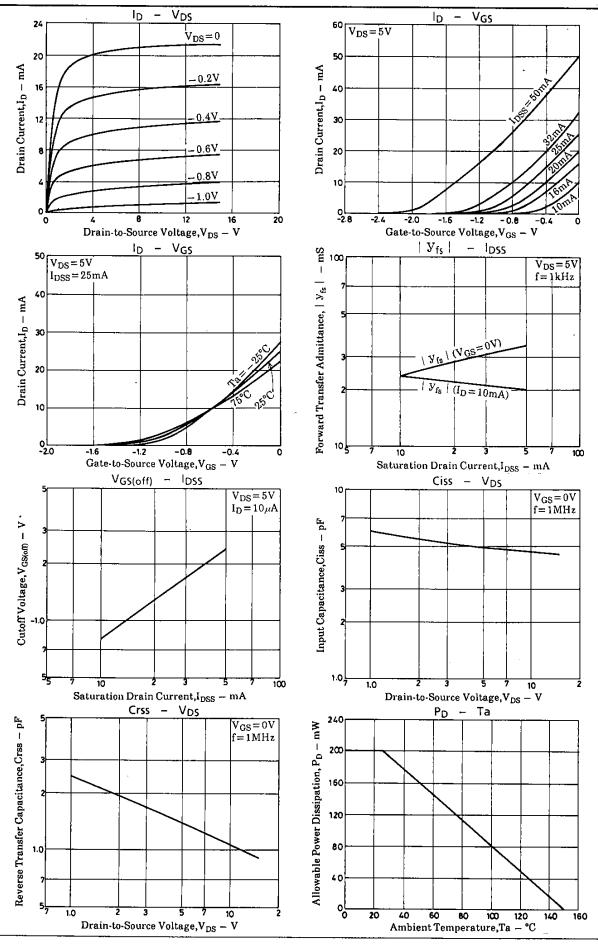
10.0 6 20.0 16.0 7 32.0 25.0 8 50.0

Marking: AK I_{DSS} rank: 6, 7, 8

Package Dimensions 2050A



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